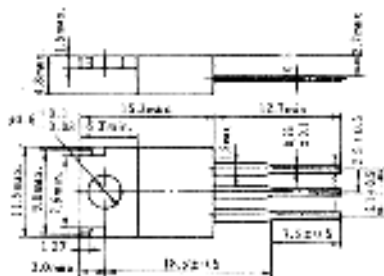


2SB856

SILICON PNP TRIPLE DIFFUSED
LOW FREQUENCY POWER AMPLIFIER



- 1. Base
- 2. Collector
- ⑥ Flange
- 3. Emitter
- ⑥ Dimensions in mm

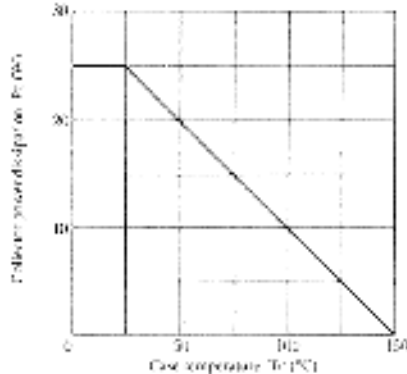
(JEDEC TO-220AB)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB856	Unit
Collector to base voltage	V _{CB0}	50	V
Collector to emitter voltage	V _{CE0}	−50	V
Emitter to base voltage	V _{EB0}	−4	V
Collector current	I _C	−1	A
Collector power dissipation	P _C *	25	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	−45 to +150	°C

* Value at T_c = 25°C

MAXIMUM COLLECTOR DISSIPATION
CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{CB0}	I _C = −5mA, I _E = 0	−50	—	—	V
Collector to emitter breakdown voltage	V _{CE0}	I _C = −50mA, R _{BE} = ∞	−50	—	—	V
Emitter to base breakdown voltage	V _{EB0}	I _E = −5mA, I _C = 0	4	—	—	V
Collector cutoff current	I _{CO}	V _{CB} = −20V, I _E = 0	—	—	−100	μA
DC current transfer ratio	h _{FE1} *	V _{CB} = −4V, I _C = −1A**	35	—	200	
	h _{FE2}	V _{CE} = −4V, I _C = −0.1A**	35	—	—	
Base to emitter voltage	V _{BE}	V _{CB} = −4V, I _C = −1A**	—	—	−1.5	V
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = −2A, I _B = −0.2A**	—	—	−1.2	V
Gain bandwidth product	f _T	V _{CE} = −4V, I _C = −0.5A**	—	35	—	MHz

* The 2SB856 is grouped by h_{FE} as follows.

** Pulse Test

A	B	C
35 to 70	60 to 120	100 to 200

2SB856

